

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prio versions, and listing, of claims in the application:

LISTING OF CLAIMS:

1. (cancelled)

2. (currently amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming a sunken section in an insulating film formed on a substrate;

forming a barrier metal film on said insulating film inclusive of said sunken section, said barrier metal film is a tantalum-based metal film;

forming a copper-based film over the entire surface so as to fill up said sunken section; and

polishing this substrate surface by the chemical mechanical polishing method to form a copper-based metal interconnection, wherein said step of polishing comprises the steps of:

a first polishing which is performed until at least a part of said barrier metal film is exposed, while using a first polishing slurry containing a silica polishing material, an oxidizing agent, an amino acid, a triazole-based compound and water, wherein a content ratio of said amino acid to said

triazole-based compound (amino acid / triazole-based compound (weight ratio)) is in a range of 5 to 8, said triazole-based compound is one of 1,2,3-triazole, 1,2,4-triazole and their derivatives, a content of said triazole-based compound is not less than 0.05 % by weight but not greater than 0.5 % by weight, said amino acid is glycine, and a pH value of said polishing slurry is in a range of 5 to 7; and

a second polishing which is performed until the surface of the insulating film other than said sunken section is exposed, while using a second polishing slurry having a composition different from the first polishing slurry.

3.-7. (cancelled)

8. (currently amended) A method of manufacturing a semiconductor device according to Claim ~~[[1]]~~ 2, wherein said silica polishing material is colloidal silica.

9.-10. (cancelled)

11. (currently amended) The method of manufacturing a semiconductor device according to Claim ~~[[10]]~~ 2, wherein a pH value of said polishing slurry is in a range of 6.5 to 7.

12. (new) The method as claimed in claim 2, wherein the second polishing slurry has a composition having a ratio of polishing rates for the copper-based metal film to the barrier metal film (copper-based metal film/barrier metal film) in a range of 0.5 to 3.

13. (new) The method as claimed in claim 12, wherein the second polishing slurry has a composition having a ratio of polishing rates for the insulating film to the barrier metal film (insulating film/barrier metal film) in a range of 0.01 to 0.5.

14. (new) The method as claimed in claim 2, wherein the second polishing slurry comprises a silica polishing material, an oxidizing agent, a polycarboxylic acid having two or more carboxy groups, and water.

15. (new) The method as claimed in claim 14, wherein the polycarboxylic acid is one of oxalic acid, malonic acid, tartaric acid, malic acid, glutaric acid, citric acid, maleic acid and their salts.

16. (new) The method as claimed in claim 2, wherein the first polishing is stopped before or when the barrier metal film other than the sunken section is completely exposed, and then the second polishing starts.